



## **Prof. Hagyoul Bae**

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Hagyoul Bae is an assistant professor in Jeonbuk National University (EE). He worked as a staff researcher in SAIT (Samsung Advanced Institute of Technology, Samsung Electronics Co., Ltd.,) from Mar 2020 to Feb 2022. From Mar 2018 to Feb 2020, He worked as a postdoctoral researcher in Purdue University (Peide D. Ye group). He received the Ph.D. degree at the KAIST, Daejeon, Korea (2018). From Mar 2007 to Jun 2009, He served in the Army as a Signal Officer from ROTC and also worked as a researcher in Kookmin University (2012-2013). He won the IEEE EDS Ph.D. Student Fellowship (2016). He is also supported by the Global Ph.D. Fellowship Program (2014-2017) from NRF Korea. His current research interests include fabrication and characterization of oxide transistors (IGZO, SSO,  $\text{Ga}_2\text{O}_3$ , and  $\text{Cu}_2\text{O}$  etc.), 3D Si-NW FETs, HZO ferroelectric logic/memory, memristor-based logic-in-memory, 2D TMDCs-based FETs, and their device physics.